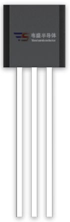
MPSA55 TRANSISTOR (PNP)



FEATURES

- General Purpose Amplifier

ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
MPSA55	**TO-92**	Bulk	1000pcs/Bag
MPSA55-TA	**TO-92**	Tape	2000pcs/Box

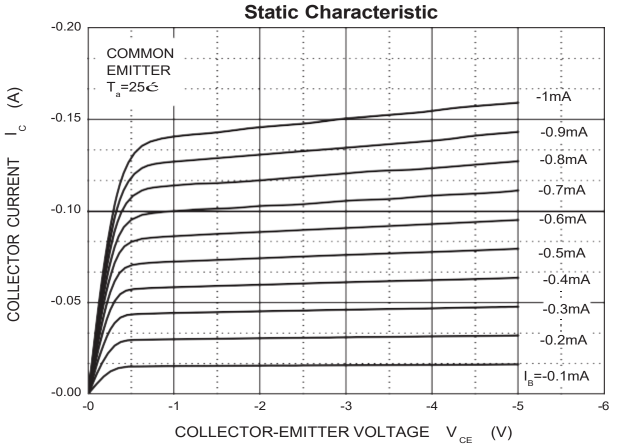
MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-4	V
I_C	Collector Current -Continuous	-0.5	A
P_D	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	200	℃ /W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

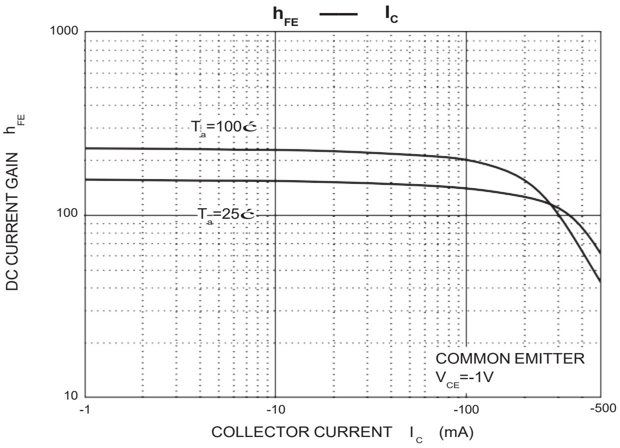
T_a=25 ℃ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= -0.1mA,I_E=0	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-0.1mA,I_C=0	-4			V
Collector cut-off current	I_{CBO}	V_{CB}=-60V,I_E=0			-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=-60V,I_B=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-4V,I_C=0			-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-1V, I_C=-10mA	100			
	$h_{FE(2)}$	V_{CE}=-1V, I_C=-100mA	100			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-100mA,I_B=-10mA			-0.25	V
Base-emitter on voltage	V_{BE}	I_C=-100mA, V_{CE}=-1V			-1.2	V
Transition frequency	f_T	V_{CE}=-1V,I_C=-100mA,f=100MHz	50			MHz

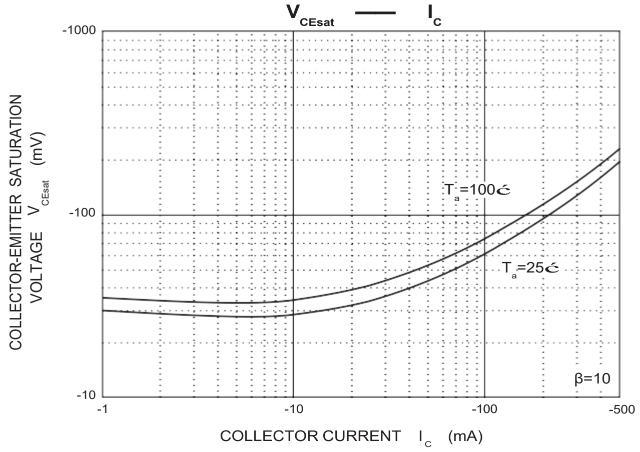
Static Characteristic



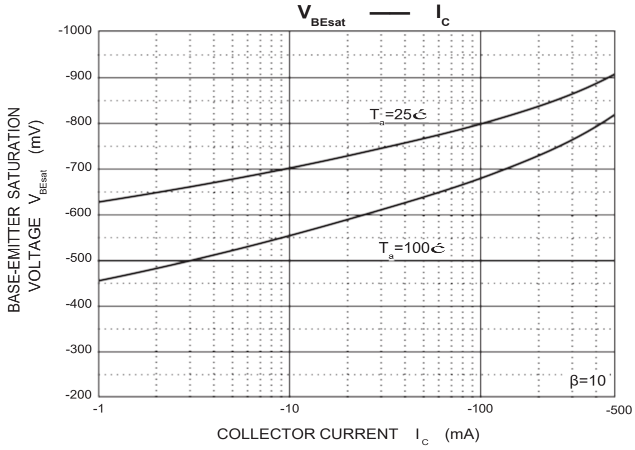
h_{FE} — I_C



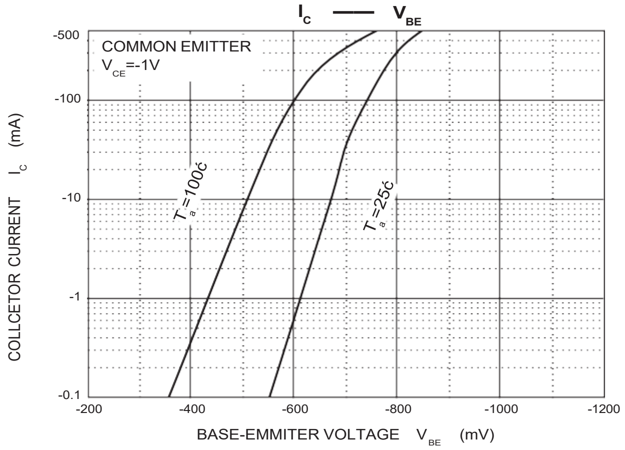
V_{CEsat} — I_C



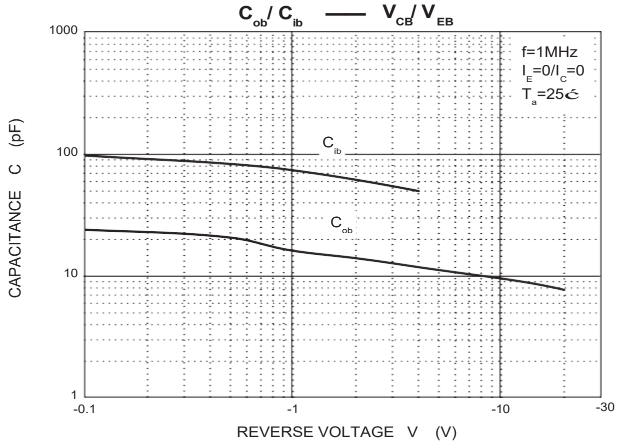
V_{BEsat} — I_C



I_C — V_{BE}



C_{ob} / C_{ib} — V_{CB} / V_{EB}



P_C — T_a